

Features

- For surface mount applications
- Glass passivated chip junction
- Low profile package
- High efficiency
- Lead free in comply with EU RoHS 2011/65/EU directive

SMA



1.Cathode —|<— 2.Anode

Marking Code:

US2A-TN:US2A
US2B-TN:US2B
US2D-TN:US2D
US2G-TN: US2G
US2J-TN:US2J
US2K-TN:US2K
US2M-TN: US2M

Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

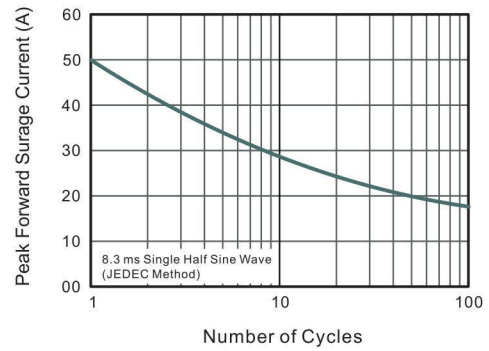
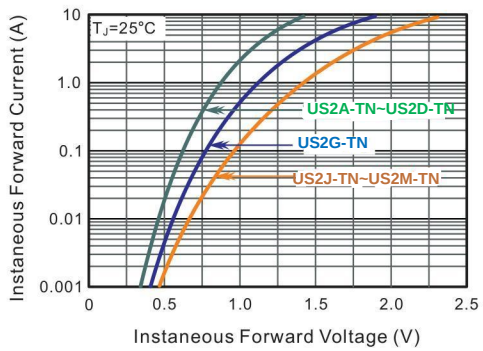
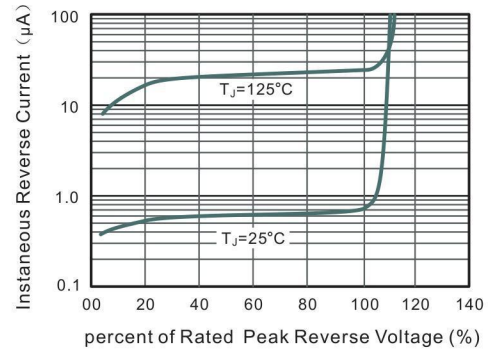
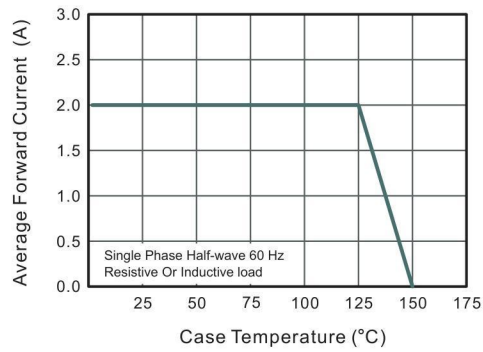
Parameter	Symbols	US2A-TN	US2B-TN	US2D-TN	US2G-TN	US2J-TN	US2K-TN	US2M-TN	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T _C =125°C	I _{F(AV)}	2.0							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I _{FSM}	50							A
Maximum Instantaneous Forward Voltage at 2 A	V _F	1.0			1.3	1.65			V
Maximum DC Reverse Current at Rated DC Blocking Voltage T _A = 25 °C T _A = 125 °C	I _R	5 100							μA
Typical Thermal Resistance ^{Note1}	R _{θJA} R _{θJC}	65 20							°C/W
Maximum Reverse Recovery Time ^{Note2}	T _{rr}	50				75			nS
Junction Temperature	T _J	150							°C
Storage Temperature Range	T _{STG}	-55 to +150							°C

Note:

1. P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

2. Measured with $I_F=0.5\text{A}$, $I_R=1\text{A}$, $t_{rr}=0.25\text{A}$.

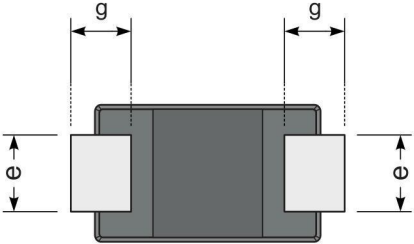
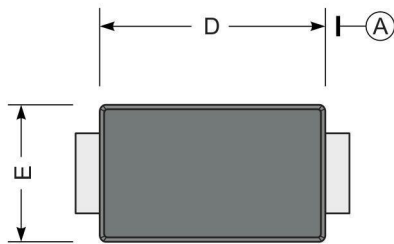
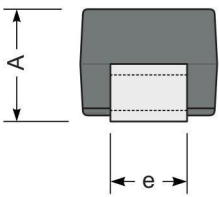
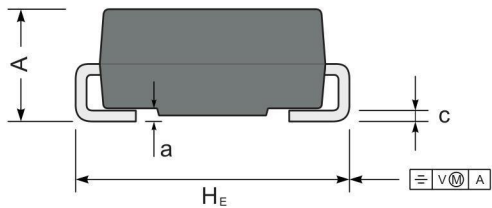
Typical Characteristic Curves



Package Outline

SMA

Dimensions in mm



UNIT		A	D	E	H _E	c	e	g	a
mm	max	2.2	4.5	2.7	5.2	0.31	1.6	1.5	0.3
	min	1.9	4.0	2.3	4.7	0.15	1.3	0.9	
mil	max	87	181	106	205	12	63	59	12
	min	75	157	91	185	6	51	35	